

YJ Planar Schottky Barrier Diode Die Specification

40V 10A, 84mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB084N040SS-280A

Main Products Characteristics

Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	40 V
Average forward current		10 A
current ($t_p = 8.3$ ms, halfwave, 1 cycle)	I_{FSM}	200 A
Storage temperature range	T_{stg}	-50 to +125 °C
Maximum operating junction temperature	T_j	125 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value
Reverse breakdown voltage	V_{BR}	SpecD 6A
$I_F = 10$ A	V_F	2%
Maximum reverse current $V_R = V_{RRM}$	I_R	60uA 25uA
		2%

Device Schematics and Outline Drawing

Die Thickness *

Die Size ** 84 Mils

Top Metal Pad 80Mils

Active Area 76 Mils

Top Metal Ag

Back Metal Ag

Note: 1 *: Also can offer device with 8 mils thickness

2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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